## YJ Planar Schottky Barrier Diode Die Specification

200V 10A, 87mil, Schottky barrier diode die based on silicon planar process

Part No.: PSB087H200AS-280A

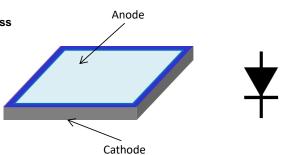
## **Main Products Characterstics**

• Average forward current: IF(AV) = 10 A

• Maximum operating junction temperature: Tj = 175 °C

• ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)

• Top metal: Al



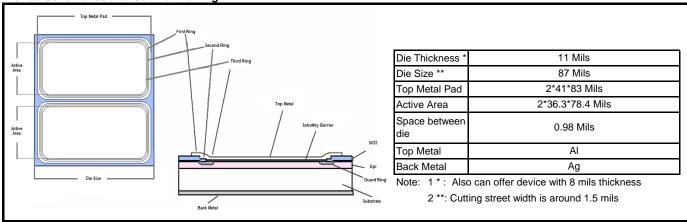
**Maximum Ratings** 

Parameter	Symbol	Rating			
Repetitive peak reverse voltage	$V_{RRM}$	200 V			
Average forward current	$I_{F(AV)}$	10 A			
Non-repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I <sub>FSM</sub>	120 A			
Storage temperature range	T <sub>stg</sub>	-50 to +175 °C			
Maximum operating junction temperature	T <sub>j</sub>	175 °C			

Static Electrical Characteristics (Ta = 25°C)

Otalio Electrical Characterictics (14 = 20 G)				
Parameter	Symbol	Value		
		Spec	Typical	
Reverse breakdown voltage $I_R = 1 \text{mA}$	$V_{BR}$	210 V	230V	
Maximum forward voltage drop				
I <sub>F</sub> = 5A	$V_{F}$	0.90V	0.84V	
Pulse Test: tp = 300 $\mu$ s, $\delta \leqslant 2\%$				
Maximum reverse current $V_R = V_{RRM}$ Pulse Test: tp = 300 µs, $\delta \le 2\%$	I <sub>R</sub>	3uA	0.2uA	

**Device Schematics and Outline Drawing** 



## **Important Notice**

Specification apply to die only. Actual performance may degrade when assembled.

Yangije Electronics does not guarantee device performance after assembly.

All operating parameters must be validated for each customer application by customer technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

扬州扬杰电子科技股份有限公司

Yangzhou Yangjie Electronics Technology Co.,Ltd.

电话: 0514-80982389 传真: 0514-80980189